

Magnetic and transport properties of the mixed-valent compound YbRh₂Ga

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We report the measurements of specific heat, electrical resistivity, magnetic susceptibility, Hall coefficient and thermoelectric power on a ternary compound of YbRh₂Ga, which crystallizes in the triple-hexagonal Na₃As-type structure with the space group $P6_3$ cm. YbRh₂Ga remains in a paramagnetic state down to 1.2 K. The magnetic susceptibility exhibits a broad maximum around 90 K for $H\parallel c$ or 170 K for $H\perp c$, respectively. Such maximum is a characteristic of the Ce- and Yb-based mixed-valent compounds. The temperature dependence of electrical resistivity shows an S -type behavior. The electronic specific heat coefficient is 36.6 mJ/molK², which is nine times larger than that of YRh₂Ga (3.9 mJ/molK²) with no $4f$ electron. The thermoelectric power ($\Delta T\parallel c$) shows a broad minimum at about 120 K with a relatively large negative value, ~ -36 μ V/K, which is typical for Yb-based spin-fluctuation systems. The Hall coefficient ($J\parallel c, H\perp c$) exhibits a maximum around 60 K; at higher temperatures it varies with temperature in a manner suggestive of skew scattering. All of the measurement results indicate that YbRh₂Ga is a typical mixed-valent system. The anisotropy observed in YbRh₂Ga indicates anisotropic hybridization between localized $4f$ -electron and conduction electrons.

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I. INTRODUCTION

It is well known that some Ce-, Sm-, Eu-, and Yb-based intermetallic compounds exhibit mixed-valent or valence-fluctuating behaviors.^{1,2} The unconventional behaviors are reflected in unit-cell volume, static dc susceptibility, electrical resistivity, etc., and are thought to result from the proximity between the energy level of the $4f$ electrons to the Fermi level and the resulting hybridization between these electrons. Recently, the new ternary compound of YbIr₂Ga with a quasi-two-dimensional (2D) structure was characterized to be in a mixed-valent state.³ The electronic specific heat is as large 21.7 mJ/molK² and the magnetic susceptibility shows a broad maximum near 180 K ($H\parallel c$) or 250 K ($H\perp c$), respectively. However, the electrical resistivity was found to be featureless. In order to further understand the formation of the mixed-valent behavior with nonmagnetic ground state in this quasi-2D system, we try to grow the single crystal of YbRh₂Ga and measure the physical properties. Here we report our preliminary results of magnetic susceptibility, specific heat, electrical resistivity, Hall coefficient and thermoelectric power in YbRh₂Ga. We found that YbRh₂Ga shows a pronounced mixed-valent or valence-fluctuating behavior. It is rather uncommon to find mixed-valent behavior in noncubic systems.

II. EXPERIMENT

The single crystals of YbRh₂Ga were grown from a Ga-flux.³ The obtained crystals were characterized by a powder x-ray diffraction method using Cu-K α radiation at room temperature. The dc electrical resistivity and Hall coefficient measurements were performed by standard four- and five-

probe methods, respectively, between 1.5 K and room temperature. The specific heat was measured by the relaxation method in zero field and in 8 T in the temperature range from 1.2 to 40 K. The magnetic susceptibility measurements were carried out in a magnetic field of 0.5 T between 1.8 and 390 K using the quantum design (SQUID) magnetometer. The thermoelectric power was measured between 2 K and room temperature using a four-wire dynamic method. All measurements were performed on the well-polished samples.

III. RESULTS AND DISCUSSION

The power x-ray diffraction pattern of YbRh₂Ga single crystals shows that the sample crystallizes in the triple-hexagonal Na₃As-type structure with the space group $P6_3$ cm.^{3,4} No traces of secondary phases were observed. The crystal structure can be described as a layered quasi-2D structure,³ in which Yb–Ga layers are separated by Rh layers stacked along the c axis. This structure indicates that YbRh₂Ga should have a large anisotropy in physical properties. The lattice parameters for YbRh₂Ga are $a=7.483 \pm 0.002$ Å and $c=9.461 \pm 0.003$ Å, obtained by a least-squares fit to the experimental data. Figure 1 shows a plot of the unit-cell volume vs rare-earth elements (Gd–Lu).⁵ A volume anomaly appears for YbRh₂Ga, which suggests the divalent or intermediate state of the Yb ions.

Figure 2 shows the temperature dependence of magnetic susceptibility with magnetic field H ($=0.5$ T) applied parallel or perpendicular to c axis in the temperature range 1.8–390 K. The susceptibility χ_{\parallel} ($H\parallel c$) is much larger than χ_{\perp} ($H\perp c$) in all of the measured temperature range. This strong anisotropy is thought to be due to anisotropic c - f mixing interaction⁶ along the a and c axis of the hexagonal

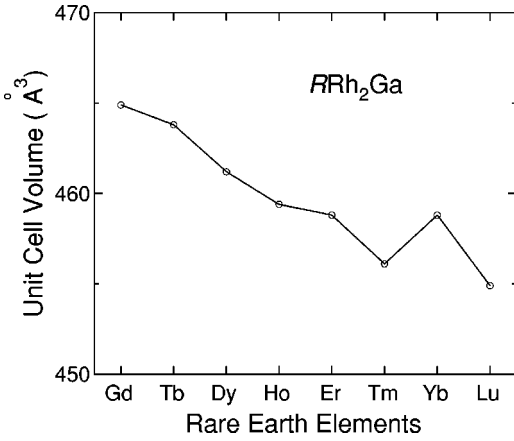


FIG. 1. Unit-cell volume vs rare-earth element in RRh_2Ga compounds.

Na_3As -type structure. The distinctive feature of $\chi(T)$ curves is a broad maximum at $T_{\max,\chi} \approx 90$ K for $H \parallel c$ and $T_{\max,\chi} \approx 170$ K for $H \perp c$, respectively. The high temperature scales, $T_{\max,\chi} \sim 100$ K, are typical of mixed-valent compounds with Kondo temperature T_K greater than 500 K.^{1,2} No impurity trail was observed in the susceptibility of $YbRh_2Ga$ at the lowest temperatures, indicating the high quality of our sample. Above 250 K, $\chi_{\parallel}(T)$ follows Curie-Weiss law, $\chi(T) = N\mu_{\text{eff}}^2/3\kappa_B(T - \Theta)$, and gives effective moment $\mu_{\text{eff}} = 3.43 \mu_B$ and Weiss temperature $\Theta = -40$ K. The value of effective moment is reduced from $4.54 \mu_B$ expected for free Yb^{3+} ions, which indicates an intermediate valence state of the Yb ions in $YbRh_2Ga$. But $\chi_{\perp}(T)$ does not exhibit Curie-Weiss behavior up to 390 K. According to the Bethe-ansatz solution of Coqblin-Schrieffer model for Kondo-impurity system,⁷ the characteristic spin-fluctuation temperature T_0 could be estimated from

$$T_0 = \nu(\nu^2 - 1)(g\mu_B)^2/24k_B\chi(0), \quad (1)$$

where ν is the magnetic degeneracy, g is the Landé g factor, μ_B is the Bohr magneton, and k_B is Boltzmann's constant.

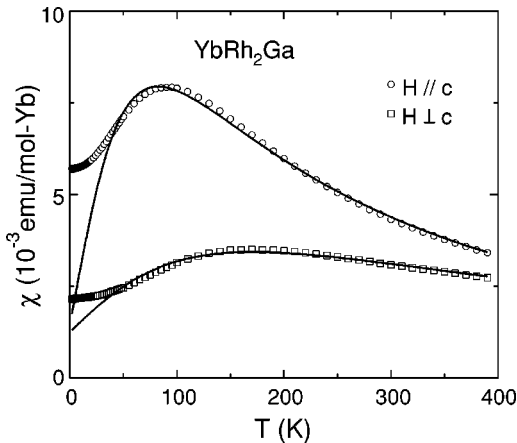


FIG. 2. Temperature dependence of magnetic susceptibility for $YbRh_2Ga$ with magnetic field ($H=0.5$ T) applied parallel or perpendicular to c axis. The solid lines are the fits of χ to the ICF model with the parameters given in the text.

$\chi(0)$ is estimated to be 5.68×10^{-3} emu/mol for $H \parallel c$ or 2.14×10^{-3} emu/mol for $H \perp c$, respectively. Taking $\nu=8$ and $g=8/7$, we get the characteristic temperature $T_0 = 577$ K for $H \parallel c$ or 1532 K for $H \perp c$, respectively, which is comparable to the value $T_0=824$ K obtained by using the equation $C/T(T \rightarrow 0) = \gamma = (\nu - 1)\pi\kappa_B/6T_0$, and $\gamma = 36.6$ mJ/molK² given in later. Rajan⁷ had given the temperature dependence of magnetic susceptibility in terms of the Bethe-ansatz solution of the Coqblin-Schrieffer model. We have tried to fit experimental data using the obtained parameters. However, in this case, the theoretical curves of $\chi(T)$ do not reproduce the experimental results well (not shown here). The disagreement may be attributed to the valency of Yb ions in $YbRh_2Ga$, which deviates strongly from +3; this point can be understood from the relatively small effective moment value. Bickers *et al.*⁸ have calculated the temperature dependence of magnetic susceptibility with the $4f$ occupation number $n_f < 1$ for $\nu=6$ and found that $\chi(T)$ deviates strongly from the case $n_f=1$.

An alternative approach describing the features of intermediate valence systems is the interconfiguration fluctuation (ICF) model.⁹ In the ICF model, the interaction of the conduction electrons with the $4f$ shell induces that the rare earth ion fluctuates between two configurations: ground state and excited state. The magnetic susceptibility of Yb ions in the ICF model can be written as

$$\chi = N(4.54\mu_B)^2\nu(T)/3\kappa_B(T + T_{sf}) + \chi_0 \quad (2)$$

and

$$\nu(T) = 8/\{8 + \exp[-E_{\text{ex}}/\kappa_B(T + T_{sf})]\}, \quad (3)$$

where E_{ex} is the energy difference between the $4f^{14}$ and $4f^{13}$ states, and T_{sf} is spin-fluctuation temperature, χ_0 is the temperature independent susceptibility. The fits of the measured data to Eqs. (2) and (3) are in reasonable agreement in the high temperature region and give $-E_{\text{ex}}/k_B = 294$ K, $T_{sf} = 62$ K and $\chi_0 = -9.3 \times 10^{-4}$ emu/mol for $H \parallel c$, or $-E_{\text{ex}}/k_B = 684$ K, $T_{sf} = 164$ K, and $\chi_0 = -4.8 \times 10^{-4}$ emu/mol for $H \perp c$, respectively. The large negative E_{ex} values indicate that the magnetic $4f^{13}$ state is situated well above the nonmagnetic $4f^{14}$ ground state. The values of E_{ex} and T_{sf} are comparable to those of well-known Yb-based compounds like $YbAl_3$.⁹ The valence of Yb ion estimated from Eq. (3) is 2.78 for $H \parallel c$ or 2.65 for $H \perp c$ at room temperature.

The temperature dependence of electrical resistivity measured with the current J parallel or perpendicular to c axis is shown in Fig. 3. The electrical resistivity increases monotonically with temperatures up to room temperature. A broad shoulder was observed at ~ 150 K for both directions. This temperature dependence resembles that of typical Yb-based mixed-valent compounds such as $YbAl_3$, which possesses a characteristic temperature $T_K \sim 670$ K.^{1,10} This relatively large T_K value is expected to overcome the crystal-electric-field (CEF) splitting. In $YbRh_2Ga$, $\rho_{\parallel}(J \parallel c)$ is much larger than $\rho_{\perp}(J \perp c)$ over all the temperatures, suggesting the high anisotropy. This anisotropy in ρ could be also considered to result from the anisotropic hybridization between localized

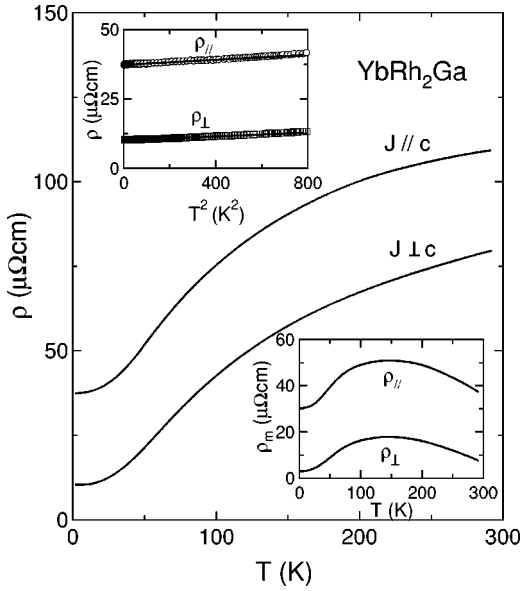


FIG. 3. Temperature dependence of electrical resistivity of YbRh₂Ga with the current parallel or perpendicular to c axis between 1.6 K and room temperature. Upper inset: The electrical resistivity vs quadratic temperature in low temperature region. The solid line shows the T^2 dependence. Lower inset: Magnetic contribution to the resistivity of YbRh₂Ga as a function of temperature obtained by subtracting the resistivity of YRh₂Ga.

4 f -electron and conduction electrons.⁶ At room temperature, $\rho_{||}$ is 110 $\mu\Omega\text{cm}$ and ρ_{\perp} is 80 $\mu\Omega\text{cm}$, respectively, which is the same order of magnitude as other known mixed-valent compounds.^{1,2} As shown in the upper inset of Fig. 3, ρ shows a T^2 -dependence up to 25 K, indicative of Fermi-liquid behavior or spin fluctuations. The fit of equation $\rho = \rho_0 + AT^2$ to the data yields the residual resistivity $\rho_0 = 37.42 \mu\Omega\text{cm}$ (10.21 $\mu\Omega\text{cm}$) and $A = 0.0047 \mu\Omega\text{cm}/\text{K}^2$ (0.0033 $\mu\Omega\text{cm}/\text{K}^2$) for $J||c$ ($J\perp c$), respectively. The A value along c axis is larger than that perpendicular to c axis. To estimate the magnetic contribution ρ_m to the electrical resistivity, we use the data of YRh₂Ga as a reference material (not shown here). We assumed that the temperature dependence of resistivity of YbRh₂Ga and the residual resistivity is approximately the same in both compounds, and then we get $\rho_m = \rho_{\text{Yb}} - \rho_{\text{Y}}$. The obtained ρ_m vs T was plotted in the lower inset of Fig. 3. The prominent feature of the magnetic resistivity is the presence of a broad maximum at $T_{\text{max},\rho_m} \approx 150$ K. Similar behaviors have been observed in many valence-fluctuating systems.^{1,11,12} In most of the cases, the temperature scale of this transport anomaly is comparable to $T_{\text{max},\chi}$ deduced from the magnetic susceptibility. Since $T_{\text{max},\chi}$ can be chosen as an order of magnitude estimate of the Ce (Yb) spin fluctuation temperature, it is natural to attribute the anomaly of resistivity to a strong Ce (Yb) spin-scattering for those compounds where $T_{\text{max},\rho_m} \approx T_{\text{max},\chi}$.¹ In YbRh₂Ga, $T_{\text{max},\chi}$ values are also comparable to T_{max,ρ_m} , and so we suggest that the transport anomaly should be accounted for by the spin-scattering mechanism, rather than the CEF splitting or Kondo scattering mechanism.

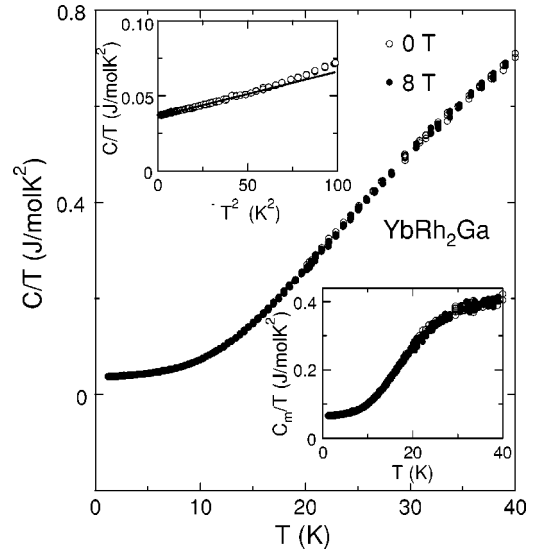


FIG. 4. Specific heat divided by temperature C/T vs temperature T for YbRh₂Ga between 1.2 and 40 K in applied magnetic fields H of 0 and 8 T ($H||c$). Upper inset: Specific heat divided by temperature C/T vs T^2 at $H=0$. The solid line is a fit of $C/T = \gamma + \beta T^2$ with the parameters given in the text. Lower inset: Magnetic contribution to the specific heat in YbRh₂Ga.

Figure 4 plots the specific heat divided by temperature C/T vs T between 1.2 and 40 K measured in zero field and in 8 T. The absence of an anomaly in $C(T)$ for YbRh₂Ga confirms that this compound does not exhibit any magnetic order, at least down to 1.2 K. The upper inset shows the plots of C/T vs T^2 in zero field. A linear dependence of C/T on T^2 was observed up to 8 K. Fitting the data to the expression $C/T = \gamma + \beta T^2$ gives $\gamma = 36.6 \text{ mJ/molK}^2$, $\beta = 0.306 \text{ mJ/molK}^4$, and Debye temperature $\theta_D = 294$ K. The γ value is nine times larger than that of YRh₂Ga (3.9 mJ/molK^2 , not shown here) with no 4 f electron and small larger than that of isostructural compound YbIr₂Ga.³ The enhanced value for YbRh₂Ga is comparable to those of known intermediate compounds: $\gamma = 45 \text{ mJ/molK}^2$ for YbAl₃,¹³ $\gamma = 135 \text{ mJ/molK}^2$ for YbCu₂Si₂,¹⁴ and $\gamma = 260 \text{ mJ/molK}^2$ for YbCuAl.¹⁵ The enhancement of the electronic specific heat in YbRh₂Ga indicates that the electronic state of the Yb ions is likely in valence fluctuating state rather than in a tri-valent state. In heavy-fermion systems, magnetic fields are expected to cause important changes, especially for the low-temperature specific heat. For example, in YbAgCu₄,¹⁶ γ increases strongly with field (by 10% at 10 T) and shows a quadratic field dependence up to 10 T. However, in our case, no distinct difference was observed between the specific heat measured in zero field and in 8 T as shown in the Fig. 4. A very small enhancement (0.1 mJ/molK^2) is consistent with the not enough large value of γ . The magnetic contribution $C_m(T)$ to specific heat for YbRh₂Ga was deduced by subtracting $C(T)$ of YRh₂Ga, as plotted in the lower inset of Fig. 4. No anomaly was observed at low temperatures. Note that a maximum or increase of C_m/T at the lowest temperatures was frequently observed in some mixed-valent compounds where a second energy

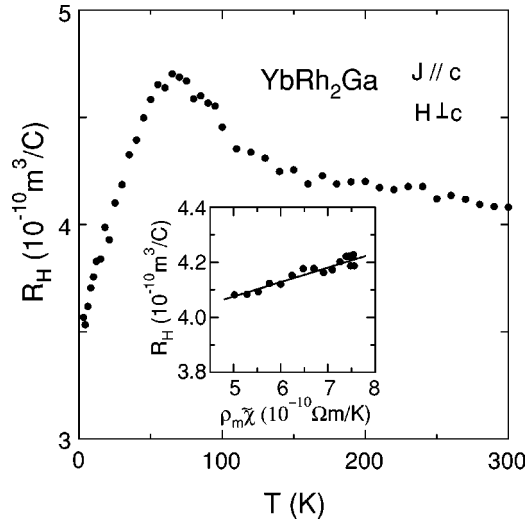


FIG. 5. Temperature dependence of Hall coefficient R_H for YbRh_2Ga with current along c axis and magnetic field applied perpendicular to c axis. Inset: Hall coefficient R_H plotted as $\rho_m\tilde{\chi}$. The solid line shows the linear dependence.

scale was developed, like YbAl_3 ¹⁰ and CeNiSi_2 .¹⁷ The estimated magnetic entropy S_m is close to $R \ln 2$ per Yb ion at 40 K.

For comparison with other heavy-fermion and mixed-valent compounds, we estimated the Kadowaki–Woods ratio¹⁸ A/γ^2 for YbRh_2Ga , where A is the coefficient of the T^2 -term of the electrical resistivity and γ is the electronic contribution to the specific heat. The values of A/γ^2 are $0.3 \times 10^{-5} \mu\Omega\text{cm}/(\text{molK/mJ})^2$ for $J\parallel c$ or $0.24 \times 10^{-5} \mu\Omega\text{cm}/(\text{molK/mJ})^2$ for $J\perp c$, respectively. These values are the same order as the common value of $1 \times 10^{-5} \mu\Omega\text{cm}/(\text{molK/mJ})^2$ for other mixed-valent compounds, like YbAl_3 ,¹⁹ which is estimated to be $0.4 \times 10^{-5} \mu\Omega\text{cm}/(\text{molK/mJ})^2$. This result confirmed that YbRh_2Ga is a typical mixed-valent compound.

Figure 5 shows the Hall coefficient R_H vs temperature T for YbRh_2Ga between 2 and 300 K measured with $J\parallel c$ and $H\perp c$ ($H=1.3$ T). R_H is positive over the measured temperature range. With decreasing temperature, R_H increases and exhibits a maximum around 65 K and followed by steep decrease toward lower temperatures. In the impurity Kondo system, the Hall coefficient can be described by the expression^{20–22}

$$R_H = R_0 + \gamma^* \rho_m \tilde{\chi}, \quad (4)$$

where R_0 is the ordinary Hall constant, $\tilde{\chi}$ is the reduced susceptibility, $\tilde{\chi} = \chi/C$ (where C is the Curie constant), γ^* is a constant and ρ_m is magnetic resistivity. The second term, the anomalous Hall coefficient, arises from skew scattering

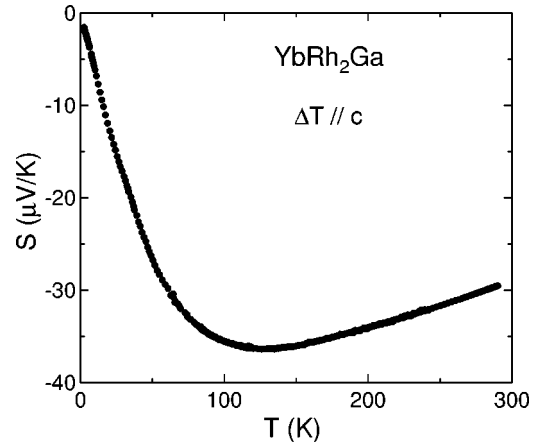


FIG. 6. Plots of thermoelectric power S vs temperature T for YbRh_2Ga with thermal gradient parallel to c axis.

of conduction electrons by Yb ions. We have tried to fit the data by using the Eq. (4). We plotted the R_H vs $\rho_m\tilde{\chi}$ in the inset of Fig. 5 in the temperature range 140–300 K. The linear dependence, shown by the solid line, gives $R_0 = 3.86 \times 10^{-10} \text{ m}^3/\text{C}$ and $\gamma^* = 0.046 \text{ K/T}$. The γ^* value is comparable to those of heavy-fermion or mixed-valent compounds.²⁰

The temperature dependence of thermoelectric power S for YbRh_2Ga with thermal gradient parallel to c axis is shown in Fig. 6. In contrast to R_H , S is negative at all temperatures. The prominent feature in the thermoelectric power is the large absolute value ($\sim -29 \mu\text{V/K}$ at room temperature) which exceeds those of simple metals by one or two orders magnitude, and exhibits a broad minimum at $T_{\min,S} \approx 120 \text{ K}$, where $S \approx -36 \mu\text{V/K}$. We found that $T_{\min,S}$ is close to $T_{\max,\chi}$ where the magnetic susceptibility shows a broad maximum. Note that the broad negative anomaly agrees with those observed in most of Yb-based mixed-valent compounds.²³ It is opposite in sign to the Ce compounds due to the electron-hole symmetry of $\text{Ce}^{3+} 4f^1$ compared with $\text{Yb}^{3+} 4f^{13}$.

In summary, our results indicate that YbRh_2Ga is a typical mixed-valent system with a magnetically nonordered ground state. This compound offers an interesting example of mixed valence in noncubic systems. The anisotropy observed in YbRh_2Ga could be attributed to the anisotropic c - f mixing along a and c axis of the hexagonal Na_3As -type structure. To understand better the anisotropic anomaly in YbRh_2Ga , it is necessary to obtain detailed information⁶ on the electronic structure near the Fermi surface.

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¹J. M. Lawrence, P. S. Riseborough, and R. D. Parks, Rep. Prog.

Phys. **44**, 1 (1981).

²P. Wachter, in *Handbook on the Physics and Chemistry of the Rare Earths*, edited by K. A. Gschneidner, Jr., L. Eyring, G. H. Lander, and G. R. Choppin (Elsevier, Amsterdam, 1994), Vol. 19, Lanthanides/Actinides: Physics—II, p. 177.

- ³C. Petrovic, M. F. Hundley, R. Movshovich, P. G. Pagliuso, J. L. Sarrao, J. D. Thompson, Z. Fisk, A. Garcia, E. Granado, I. Torriani, and C. Rettori, *J. Magn. Magn. Mater.* **225**, 317 (2001); C. Petrovic, M. F. Hundley, R. Movshovich, P. G. Pagliuso, J. L. Sarrao, J. D. Thompson, and Z. Fisk, *J. Alloys Compd.* **325**, 1 (2001).
- ⁴P. Hafner and K. J. Range, *J. Alloys Compd.* **216**, 7 (1994); K. J. Range, R. Ehrl, and P. Hafner, *ibid.* **240**, 19 (1996).
- ⁵G. F. Chen, S. Ohara, and I. Sakamoto (unpublished).
- ⁶See, for example, B. R. Cooper, R. Siemann, D. Yang, P. Thayamballi, and A. Banerjea, in *Handbook on the Physics and Chemistry of the Actinides*, edited by A. J. Freeman and G. H. Lander (Elsevier, New York, 1985), Vol. 2, p. 415; B. R. Cooper, J. M. Wills, N. Kioussis, and Q. G. Sheng, *J. Appl. Phys.* **64**, 5587 (1988); S. Zhang and P. M. Levy, *Phys. Rev. B* **40**, 7179 (1989); P. M. Levy and S. Zhang, *Phys. Rev. Lett.* **62**, 78 (1983).
- ⁷V. T. Rajan, *Phys. Rev. Lett.* **51**, 308 (1983).
- ⁸N. E. Bickers, D. L. Cox, and J. W. Wilkins, *Phys. Rev. B* **36**, 2036 (1987).
- ⁹B. C. Sales and D. K. Wohlleben, *Phys. Rev. Lett.* **35**, 1240 (1975).
- ¹⁰A. L. Comelius, J. M. Lawrence, T. Ebihara, P. S. Riseborough, C. H. Booth, M. F. Hundley, P. G. Pagliuso, J. L. Sarrao, J. D. Thompson, M. H. Jung, A. H. Lacerda, and G. H. Kwei, *Phys. Rev. Lett.* **88**, 117201 (2002).
- ¹¹W. H. Lee, H. C. Ku, and R. N. Shelton, *Phys. Rev. B* **36**, 5739 (1987).
- ¹²D. T. Adroja, S. K. Malik, B. D. Padalia, and R. Vijayaraghavan, *Phys. Rev. B* **39**, 4831 (1989).
- ¹³E. E. Havinga, K. H. Buschow, and H. J. van Daal, *Solid State Commun.* **13**, 621 (1973).
- ¹⁴B. C. Sales and R. Viswanathan, *J. Low Temp. Phys.* **23**, 449 (1976).
- ¹⁵R. Pott, R. Schefzyk, D. Wohlleben, and A. Junod, *Z. Phys. B: Condens. Matter* **44**, 17 (1984).
- ¹⁶T. Graf, J. M. Lawrence, M. F. Hundley, J. D. Thompson, A. Lacerda, E. Haanappel, M. S. Torikachvili, Z. Fisk, and P. C. Canfield, *Phys. Rev. B* **51**, 15053 (1995).
- ¹⁷E. D. Mun, Y. S. Kwon, and M. H. Jung, *Phys. Rev. B* **67**, 033103 (2003).
- ¹⁸K. Kadowaki and S. B. Woods, *Solid State Commun.* **58**, 507 (1986).
- ¹⁹S. Ohara, G. F. Chen, and I. Sakamoto, *J. Alloys Compd.* **323–324**, 632 (2001).
- ²⁰A. Fert and P. M. Levy, *Phys. Rev. B* **36**, 1907 (1987).
- ²¹P. Coleman, P. W. Anderson, and T. V. Ramakrishnan, *Phys. Rev. Lett.* **55**, 414 (1985).
- ²²E. Cattaneo, *Z. Phys. B: Condens. Matter* **64**, 317 (1986).
- ²³See, for example, E. Bauer, *Adv. Phys.* **40**, 417 (1991).